

900V XPT™ IGBT GenX3™

IXYY8N90C3 IXYP8N90C3

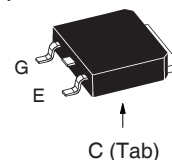
High-Speed IGBT
for 20-50 kHz Switching



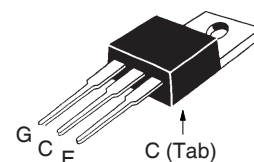
$V_{CES} = 900V$
 $I_{C110} = 8A$
 $V_{CE(sat)} \leq 3.0V$
 $t_{fi(typ)} = 130ns$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $175^\circ C$	900	V
V_{CGR}	$T_J = 25^\circ C$ to $175^\circ C$, $R_{GE} = 1M\Omega$	900	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$	20	A
I_{C110}	$T_C = 110^\circ C$	8	A
I_{CM}	$T_C = 25^\circ C$, 1ms	48	A
I_A	$T_C = 25^\circ C$	4	A
E_{AS}	$T_C = 25^\circ C$	15	mJ
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 150^\circ C$, $R_G = 30\Omega$ Clamped Inductive Load	$I_{CM} = 16$ @ $V_{CE} \leq V_{CES}$	A
P_C	$T_C = 25^\circ C$	125	W
T_J		-55 ... +175	$^\circ C$
T_{JM}		175	$^\circ C$
T_{stg}		-55 ... +175	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
M_d	Mounting Torque (TO-220)	1.13/10	Nm/lb.in.
Weight	TO-252	0.35	g
	TO-220	3.00	g

TO-252 (IXYY)



TO-220 (IXYP)



G = Gate C = Collector
E = Emitter Tab = Collector

Features

- Optimized for Low Switching Losses
- Square RBSOA
- Positive Thermal Coefficient of $V_{ce(sat)}$
- Avalanche Rated
- International Standard Packages

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

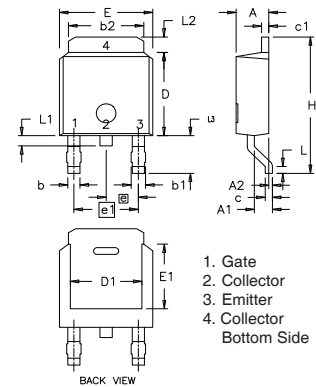
- High Frequency Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	950		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	3.5		6.0 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 150^\circ C$			10 μA 150 μA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 8A$, $V_{GE} = 15V$, Note 1 $T_J = 150^\circ C$	2.15 2.75		3.00 V V

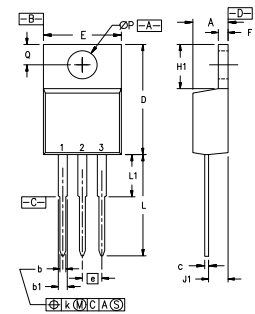
Symbol Test Conditions		Characteristic Values		
(T _J = 25°C Unless Otherwise Specified)		Min.	Typ.	Max.
g_{fs}	I _C = 8A, V _{CE} = 10V, Note 1	2.9	4.8	S
C_{ies}	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz		400	pF
C_{oes}			24	pF
C_{res}			7.8	pF
Q_{g(on)}	I _C = 8A, V _{GE} = 15V, V _{CE} = 0.5 • V _{CES}		13.3	nC
Q_{ge}			3.4	nC
Q_{gc}			5.8	nC
t_{d(on)}	Inductive load, T_J = 25°C		16	ns
t_{ri}			20	ns
E_{on}		I _C = 8A, V _{GE} = 15V	0.46	mJ
t_{d(off)}	V _{CE} = 0.5 • V _{CES} , R _G = 30Ω		40	ns
t_{fi}	Note 2		130	ns
E_{off}		0.18	0.50	mJ
t_{d(on)}	Inductive load, T_J = 125°C		17	ns
t_{ri}			22	ns
E_{on}		I _C = 8A, V _{GE} = 15V	1.00	mJ
t_{d(off)}	V _{CE} = 0.5 • V _{CES} , R _G = 30Ω		75	ns
t_{fi}	Note 2		163	ns
E_{off}		0.22		mJ
R_{thJC}				1.20 °C/W
R_{thCS}	TO-252	0.35		°C/W
	TO-220	0.50		°C/W

Notes:

1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.
2. Switching times & energy losses may increase for higher V_{CE}(clamp), T_J or R_G.

TO-252 AA Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	2.19	2.38	0.086	0.094
A1	0.89	1.14	0.035	0.045
A2	0	0.13	0	0.005
b	0.64	0.89	0.025	0.035
b1	0.76	1.14	0.030	0.045
b2	5.21	5.46	0.205	0.215
c	0.46	0.58	0.018	0.023
c1	0.46	0.58	0.018	0.023
D	5.97	6.22	0.235	0.245
D1	4.32	5.21	0.170	0.205
E	6.35	6.73	0.250	0.265
E1	4.32	5.21	0.170	0.205
e	2.28 BSC		0.090 BSC	
e1	4.57 BSC		0.180 BSC	
H	9.40	10.42	0.370	0.410
L	0.51	1.02	0.020	0.040
L1	0.64	1.02	0.025	0.040
L2	0.89	1.27	0.035	0.050
L3	2.54	2.92	0.100	0.115

TO-220 Outline


Pins: 1 - Gate 2 - Collector
3 - Emitter

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

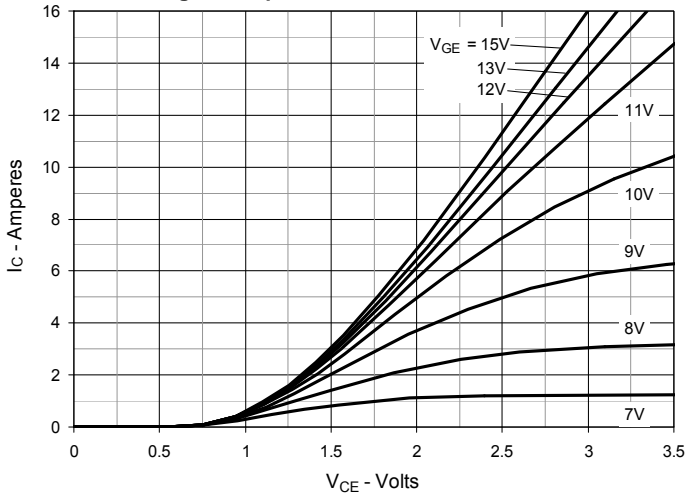


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

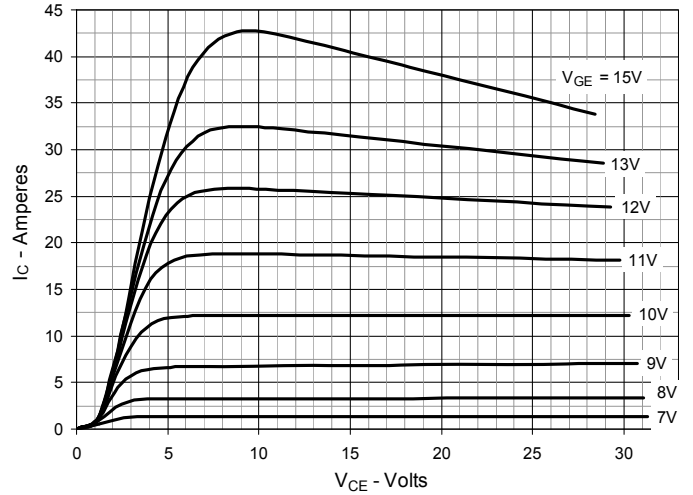


Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

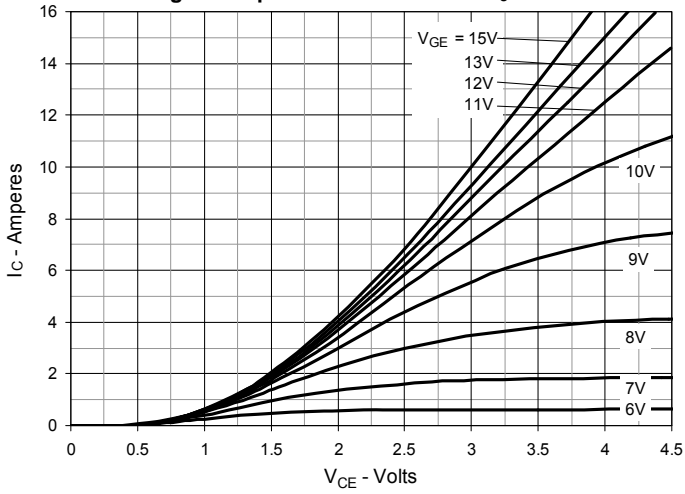


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

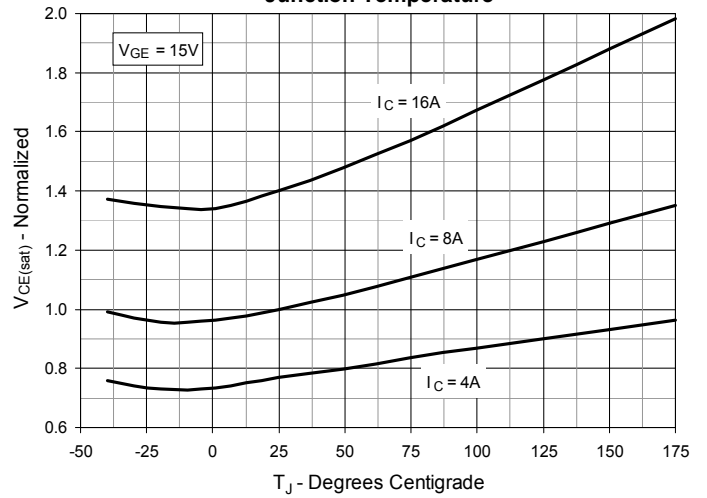


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

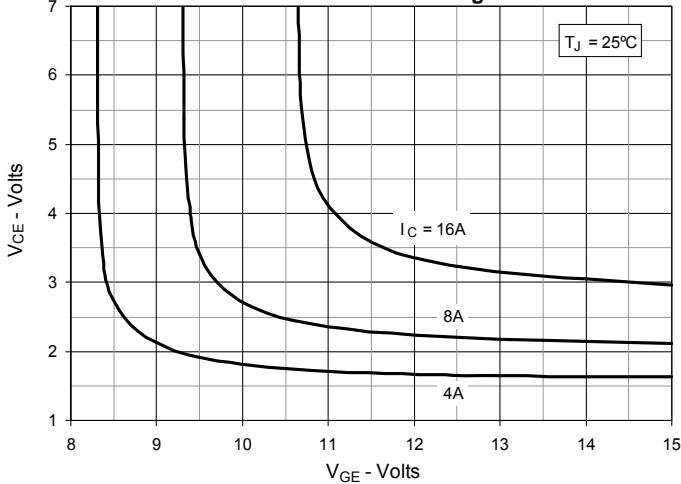


Fig. 6. Input Admittance

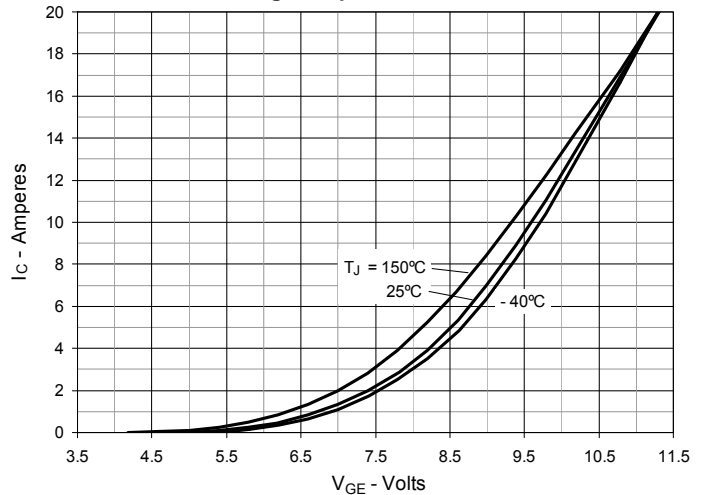


Fig. 7. Transconductance

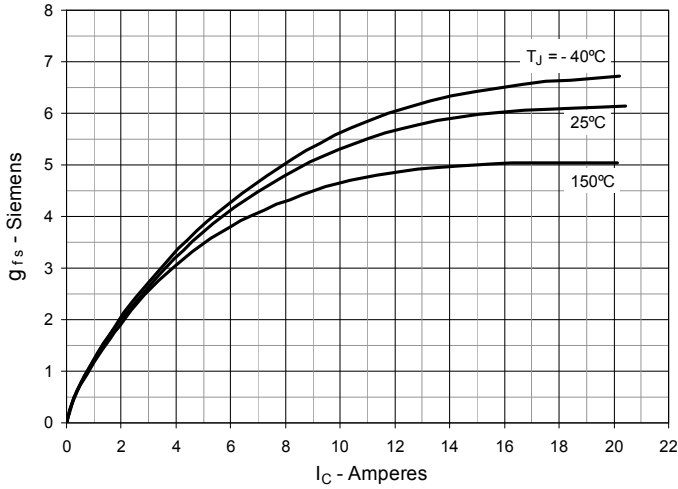


Fig. 8. Gate Charge

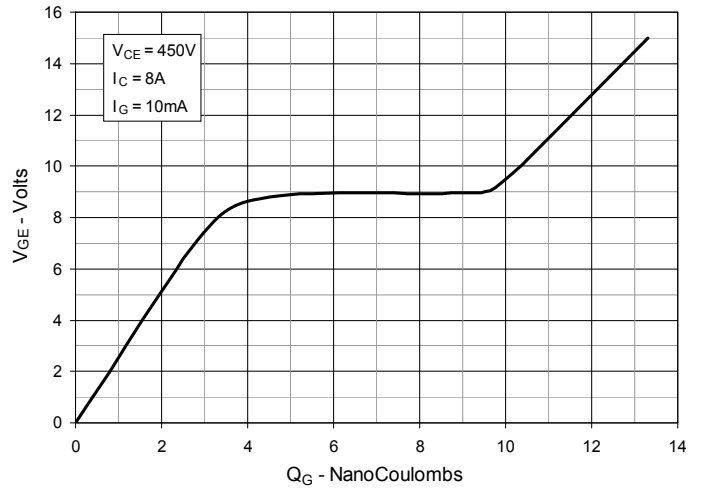


Fig. 9. Capacitance

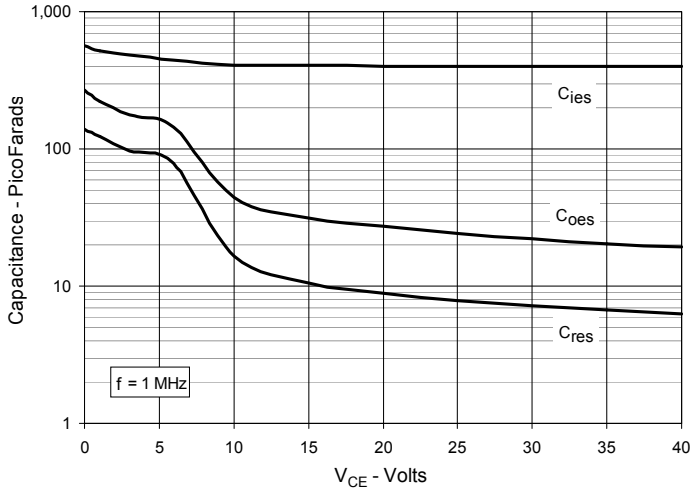


Fig. 10. Reverse-Bias Safe Operating Area

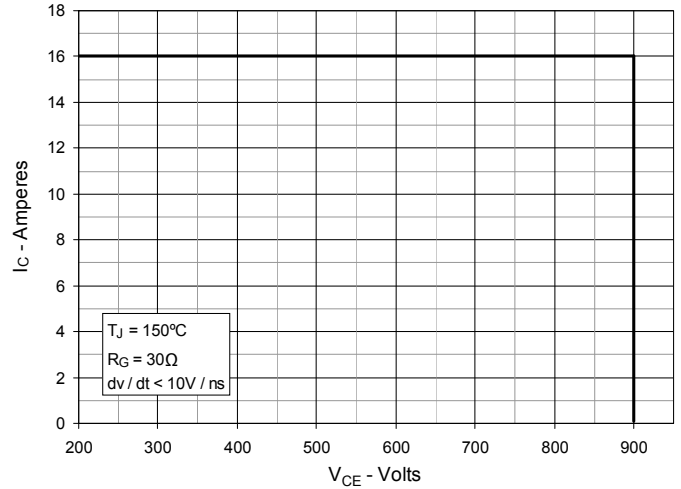


Fig. 11. Maximum Transient Thermal Impedance

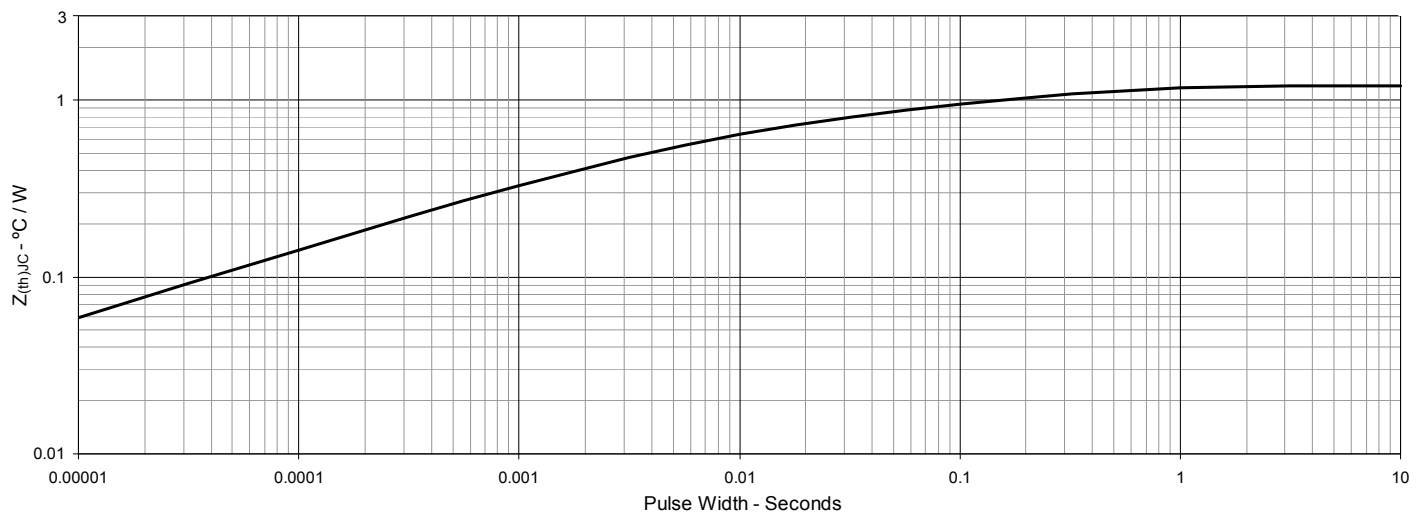


Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

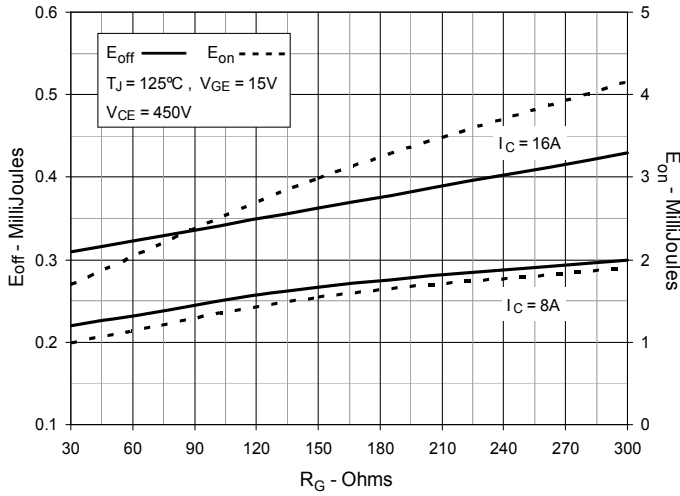


Fig. 13. Inductive Switching Energy Loss vs. Collector Current

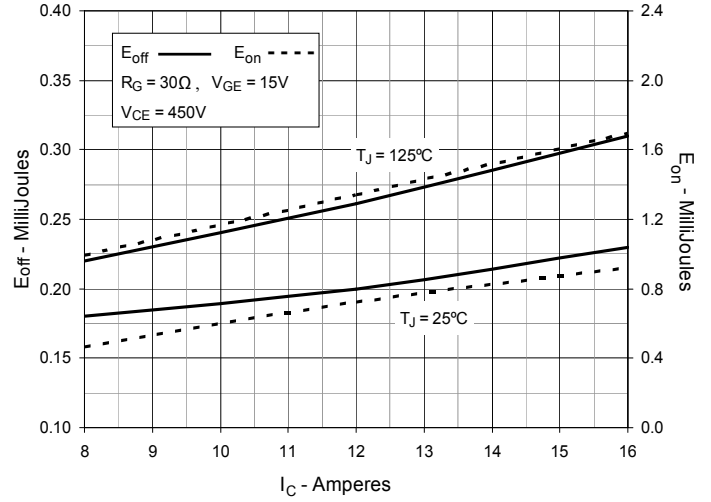


Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature



Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance



Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

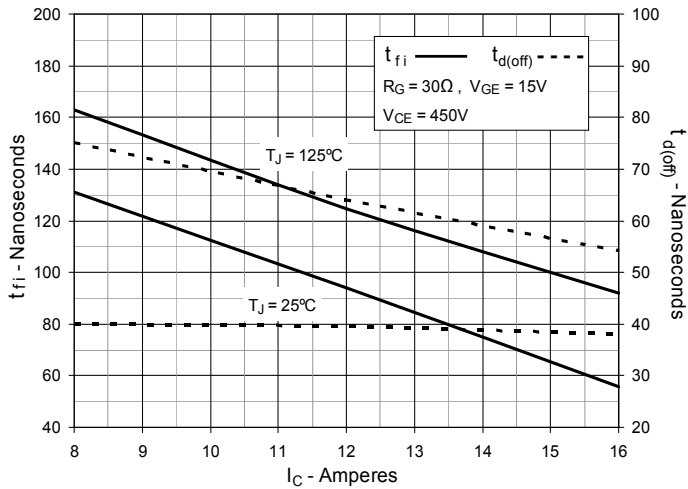


Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature

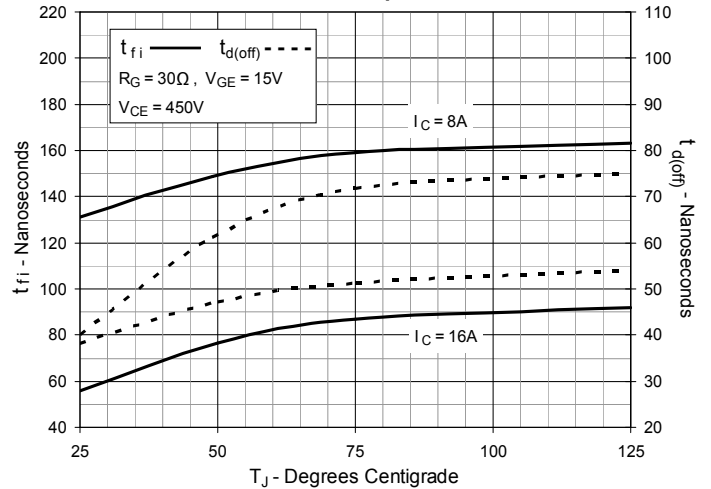


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance



Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

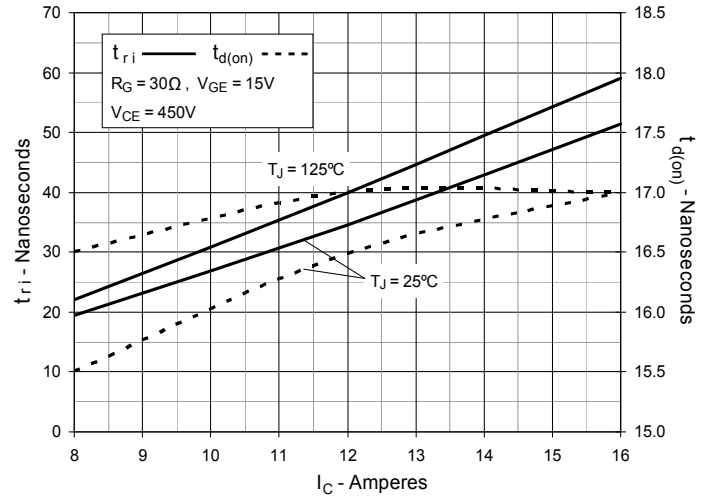


Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature

